

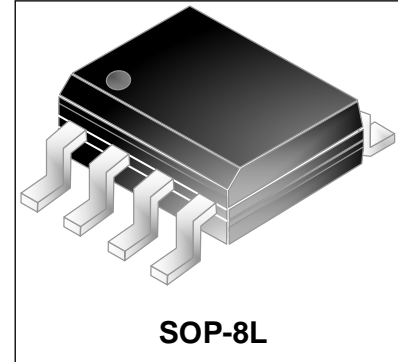


WM02DN48A

Dual N-Channel MOSFET

Features

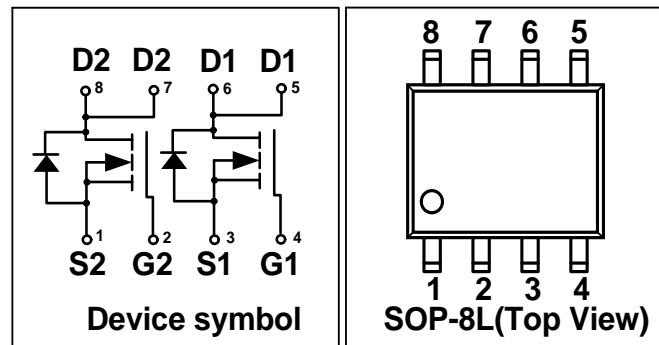
- $V_{DS} = 20V$, $I_D = 4.8A$
 $R_{DS(on)} < 30m\Omega @ V_{GS} = 4.5V$
 $R_{DS(on)} < 40m\Omega @ V_{GS} = 2.5V$
- Trench Power MOSFET
- Fast Switching Speed
- Low On-Resistance
- Green Device Available



Mechanical Characteristics

- SOP-8L Package
- Marking : Making Code
- RoHS Compliant

Schematic & PIN Configuration



Absolute Maximum Rating

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	4.8	A
Pulsed Drain Current ²	I_{DM}	30	
Power Dissipation	P_D	1.25	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55 to +150	
Thermal Resistance from Junction-to-Ambient ¹	$R_{\theta JA}$	100	°C/W

Electrical Characteristics ($T_{amb}=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20	-	-	V
Gate-body Leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 12V$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$	-	-	1	μA
Gate-Threshold Voltage ³	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	0.7	1.2	V
Drain-Source On-Resistance ³	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 4.8A$	-	20	30	m Ω
		$V_{GS} = 2.5V, I_D = 4A$	-	25	40	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$	-	515	-	pF
Output Capacitance	C_{oss}		-	73	-	
Reverse Transfer Capacitance	C_{rss}		-	65	-	
Switching Characteristics						
Total Gate Charge ⁴	Q_g	$V_{GS} = 4.5V, I_D = 3A, V_{DS} = 10V$	-	10	-	nC
Gate-Source Charge ⁴	Q_{gs}		-	1.5	-	
Gate-Drain Charge ⁴	Q_{gd}		-	1.6	-	
Turn-On Delay Time ⁴	$t_{d(on)}$	$V_{GEN} = 4.5V, V_{DD} = 10V, I_D = 1A, R_{GEN} = 6\Omega$	-	8	-	nS
Turn-On Rise Time ⁴	t_r		-	9	-	
Turn-Off Delay Time ⁴	$t_{d(off)}$		-	15	-	
Turn-Off Fall Time ⁴	t_f		-	4	-	
Source-Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$I_S = 1.7A, V_{GS} = 0V$	-	-	1.2	V

Notes

1. Repetitive rating: Pulse width limited by junction temperature.
2. Surface mounted on FR4 board, $t_s \leq 10s$.
3. Pulse Test: Pulse Width $\leq 80\mu s$, Duty Cycle $\leq 0.5\%$.
4. Guaranteed by design, not subject to production.

Typical Characteristics

Figure 1. Output Characteristics

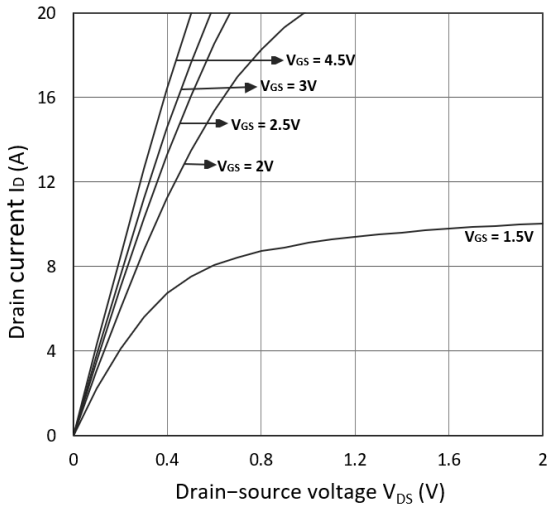


Figure 2. Transfer Characteristics

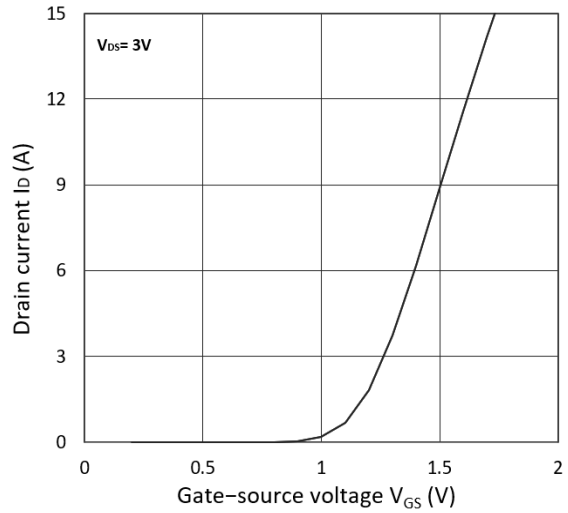


Figure 3. $R_{DS(on)}$ vs. I_D

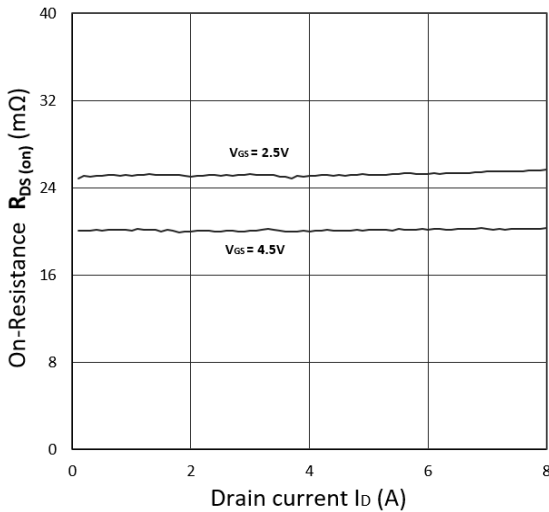


Figure 4. $R_{DS(on)}$ vs. V_{GS}

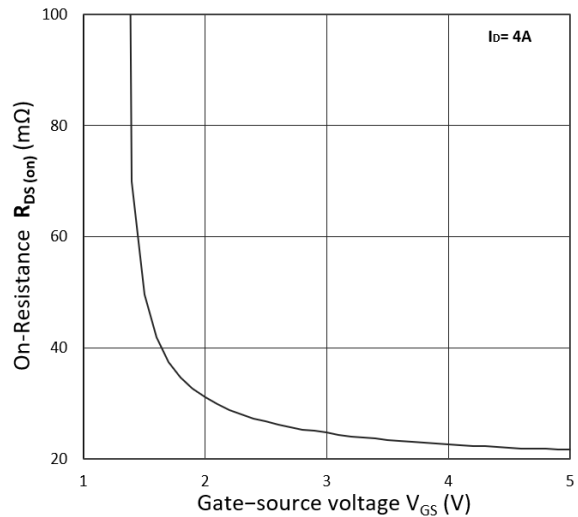


Figure 5. I_S vs. V_{SD}

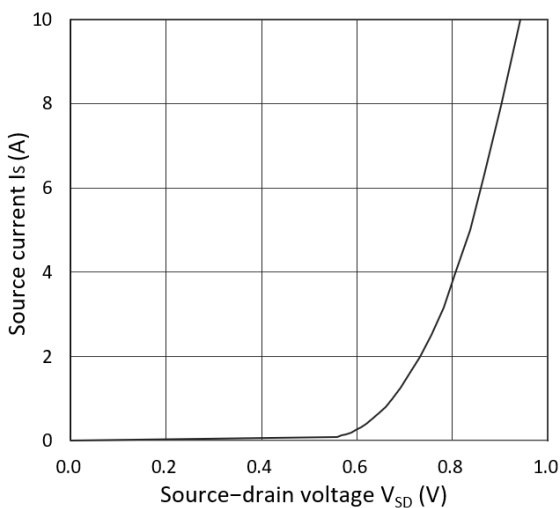
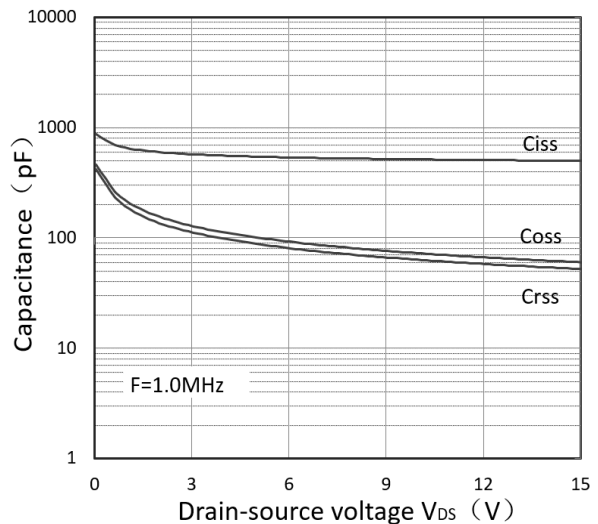


Figure 6. Capacitance Characteristics



Outline Drawing – SOP-8L

PACKAGE OUTLINE

SOP-8L

DIMENSIONS				
SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	1.23	1.75	0.048	0.069
a1	0.05	0.25	0.002	0.010
b	0.31	0.51	0.012	0.020
b1	0.16	0.25	0.006	0.010
D	4.70	5.15	0.185	0.203
E	5.75	6.25	0.226	0.246
e	1.07	1.47	0.042	0.058
F	3.70	4.10	0.146	0.161
L	0.40	1.27	0.016	0.050

Notes

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WM02DN48A
Marking Code	

Package Information

Qty: 4k/Reel

CONTACT INFORMATION

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Specifications are subject to change without notice.
 The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
 Users should verify actual device performance in their specific applications.